

No.659K

2SK223

N-Channel Silicon Junction FET

High Voltage Driver Applications

Features

- · Ultrahigh withstand voltage ($V_{GDS} \ge -80V$).
- · Due to low gate leakage currents even at high voltages, the 2SK223 is suitable for a wide range of applications ($I_{GDL} = 1nA/V_{DS} = 50V$, $I_{D} = 1mA$).
- · High $| Y_{fs} | (| Y_{fs} | = 20 \text{mS/V}_{DS} = 30 \text{V}, f = 1 \text{kHz}).$

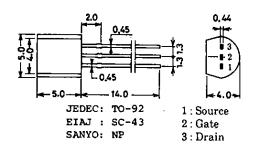
Absolute Maximum Ratings at'	$\Gamma a = 25^{\circ}C$		unit
Drain-to-Source Voltage	$V_{ m DSS}$	80	v
Gate-to-Drain Voltage	$ m v_{GDS}$	80	V
Gate Current	$I_{\mathbf{G}}$	10	mA
Allowable Power Dissipation	$P_{\mathbf{D}}$	400	mW
Junction Temperature	Tj	125	$^{\circ}\mathrm{C}$
Storage Temperature	Tstg	-40 to + 125	$^{\circ}\mathrm{C}$

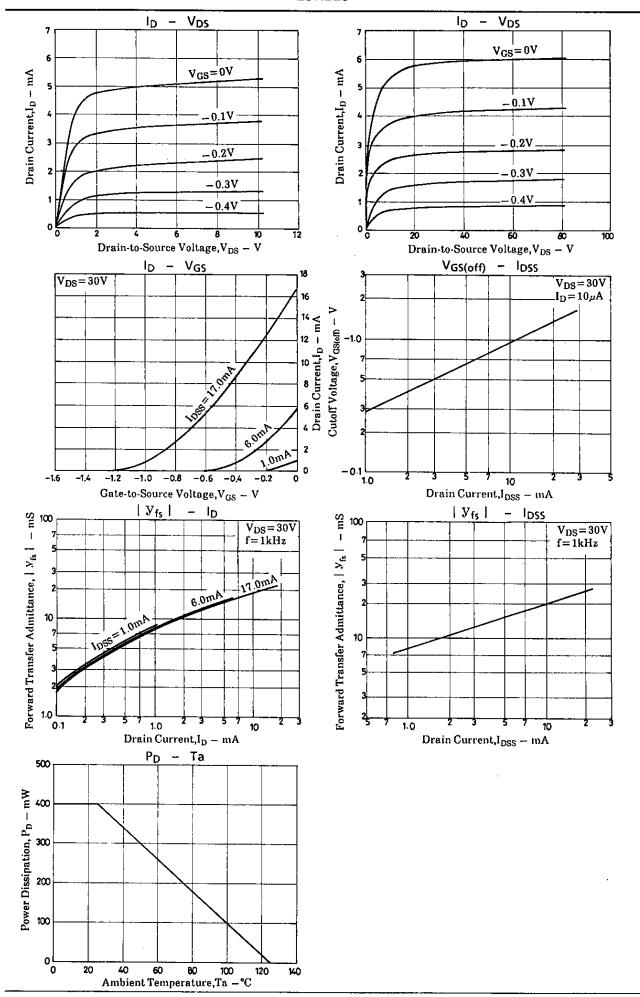
Electrical Characteristics at Ta=	25°C		min t	yp max	unit
Gate-to-Drain	$V_{(BR)GDS}$	$I_{G} = -100 \mu A$	-80	, .	V
Breakdown Voltage					
Gate Cutoff Current	I_{GSS}	$V_{GS} = -30V, V_{DS} = 0$		-1.0	nΑ
Drain Current	I_{DSS}	$V_{DS} = 30 V$, $V_{GS} = 0$	1.2*	24※	mA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 30V, I_D = 10 \mu A$	-0.78	5	V
Forward Transfer Admittance	$\mid \mathbf{y}_{\mathrm{fs}} \mid$	$V_{DS} = 30 V, V_{GS} = 0, f = 1 kHz$	20	C	mS
Input Capacitance	Ciss	$V_{DS} = 30V, V_{GS} = 0, f = 1MHz$	13	2	рF
Reverse Transfer Capacitance	Crss	$V_{DS} = 30V, V_{GS} = 0, f = 1MHz$	2.	5	pF
Noise Figure	NF	$V_{DS} = 10V, I_D = 3mA, Rg = 10k\Omega,$	1.5	5	dΒ
		f = 1kHz			

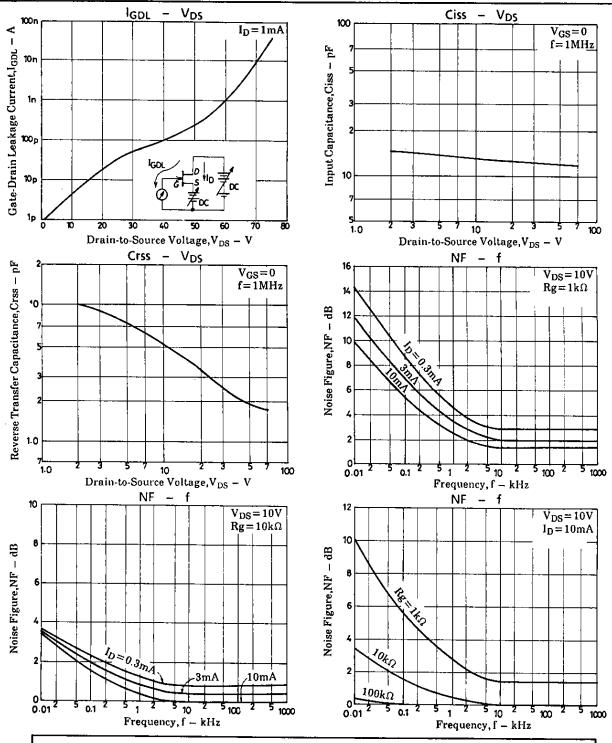
 \divideontimes The 2SK223 is classified by I_{DSS} as follows (unit: mm):

1.2 D 3.0	2.5 E 6.0	5.0 F 12.0	10.0 G 24.0

Package Dimensions 2019B (unit: mm)







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